

L Number	Hits	Search Text	DB	Time stamp
1	1	("6190988").PN.	USPAT	2004/04/13 17:22
-	3	(bottle adj trench) and (bottle adj shaped adj trenches) and DRAM	USPAT	2004/04/13 16:30
-	1		USPAT	2004/04/13 16:37
-	1		USPAT	2004/04/13 16:25
-	1		USPAT	2004/04/13 16:25
-	1		USPAT	2004/04/13 16:26
-	1		USPAT	2004/04/13 16:26
-	1		USPAT	2004/04/13 16:27
-	1		USPAT	2004/04/13 16:27
-	1		USPAT	2004/04/13 16:27
-	1		USPAT	2004/04/13 16:28
-	1		USPAT	2004/04/13 16:28
-	1		USPAT	2004/04/13 16:29
-	1		USPAT	2004/04/13 16:29
-	3	((bottle adj trench) and (bottle adj shaped adj trenches) and DRAM) and (memory or hard or mask or substrate or opening or trnch or trenches or portion or upper or isolated or isolation or Isolator or shield or polysilicon or lower or side or wall or walls or protective or bottle or shaped or part or parts or removing or etch or etching or silicon or nitride or dopant or doped or CVD or thermal or treatment or anisotropic or expose or exposed)	USPAT	2004/04/13 16:37
-	1	("5658816").PN.	USPAT	2004/04/13 16:37
-	3	((bottle adj trench) and (bottle adj shaped adj trenches) and DRAM) and (memory or hard or mask or substrate or opening or trnch or trenches or portion or upper or isolated or isolation or Isolator or shield or polysilicon or lower or side or wall or walls or protective or bottle or shaped or part or parts or removing or etch or etching or silicon or nitride or dopant or doped or CVD or thermal or treatment or anisotropic or expose or exposed)) and (memory or hard or mask or substrate or opening or trnch or trenches or portion or upper or isolated or Isolation or Isolator or shield or polysilicon or lower or side or wall or walls or protective or bottle or shaped or part or parts or removing or etch or etching or silicon or nitride or dopant or doped or CVD or thermal or treatment or anisotropic or expose or exposed)	USPAT	2004/04/13 16:38
-	1	("5629226").PN.	USPAT	2004/04/13 16:38
-	1	((("5629226").PN.) and (memory or hard or mask or substrate or opening or trnch or trenches or portion or upper or isolated or Isolation or Isolator or shield or polysilicon or lower or side or wall or walls or protective or bottle or shaped or part or parts or removing or etch or etching or silicon or nitride or dopant or doped or CVD or thermal or treatment or anisotropic or expose or exposed)	USPAT	2004/04/13 16:41
-	1	("6313008").PN.	USPAT	2004/04/13 16:41
-	1	((("5629226").PN.) and (memory or hard or mask or substrate or opening or trnch or trenches or portion or upper or isolated or isolation or Isolator or shield or polysilicon or lower or side or wall or walls or protective or bottle or shaped or part or parts or removing or etch or etching or silicon or nitride or dopant or doped or CVD or thermal or treatment or anisotropic or expose or exposed)) and (memory or hard or mask or substrate or opening or trnch or trenches or portion or upper or isolated or isolation or Isolator or shield or polysilicon or lower or side or wall or walls or protective or bottle or shaped or part or parts or removing or etch or etching or sillcon or nitride or dopant or doped or CVD or thermal or treatment or anisotropic or expose or exposed)	USPAT	2004/04/13 16:50

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-	1	("6232171").PN.	USPAT	2004/04/13 16:50
-	1	((("6232171").PN.) and (memory or hard or mask or substrate or opening or trnch or trenches or portion or upper or isolated or Isolation or isolator or shield or polysilicon or lower or side or wall or walls or protective or bottle or shaped or part or parts or removing or etch or etching or silicon or nitride or dopant or doped or CVD or thermal or treatment or anisotropic or expose or exposed)	USPAT	2004/04/13 17:22

4/13/04